# BT145X-800R

## SCR

4 September 2018 Product data sheet

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT186A (TO-220F) plastic package intended for use in applications requiring high bidirectional blocking voltage capability, high current inrush capability and high thermal cycling performance.

## 2. Features and benefits

- AC power control
- High bidirectional blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Package meets UL1557 isolation test requirement rated at 2500V RMS
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant
- Very high immunity to false turn-on by dv/dt and IEC 61000-4-4 fast transient

## 3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

## 4. Quick reference data

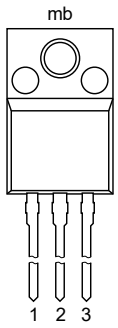
**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{RRM}$ | repetitive peak reverse voltage | | | - | - | 800 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave | | - | - | 16 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_h \leq 30$ °C; Fig. 1; Fig. 2; Fig. 3 | | - | - | 25 | A |
| $I_{TSM}$ | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5 | | - | - | 300 | A |
| | | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms | | - | - | 330 | A |
| $T_j$ | junction temperature | | | - | - | 125 | °C |
| **Static characteristics** | | | | | | | |

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $I_{GT}$ | gate trigger current | $V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C; Fig. 7 | | - | - | 35 | mA |
| **Dynamic characteristics** | | | | | | | |
| $dV_D/dt$ | rate of rise of off-state voltage | $V_{DM}$ = 536 V; $T_j$ = 125 °C; exponential waveform; gate open circuit | | 200 | - | - | V/µs |

## 5. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | K | cathode |   **TO-220F (SOT186A)** |   |
| 2 | A | anode | | |
| 3 | G | gate | | |
| mb | n.c. | mounting base; isolated | | |

## 6. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| BT145X-800R | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

# 7. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DRM}$ | repetitive peak off-state voltage | | | - | 800 | V |
| $V_{RRM}$ | repetitive peak reverse voltage | | | - | 800 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave | | - | 16 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_h \leq 30$ °C; Fig. 1; Fig. 2; Fig. 3 | | - | 25 | A |
| $I_{TSM}$ | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5 | | - | 300 | A |
| | | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms | | - | 330 | A |
| $I^2t$ | $I^2t$ for fusing | $t_p = 10$ ms; SIN | | - | 450 | $A^2s$ |
| $dI_T/dt$ | rate of rise of on-state current | $I_G = 70$ mA | | - | 200 | A/µs |
| $I_{GM}$ | peak gate current | | | - | 5 | A |
| $V_{RGM}$ | peak reverse gate voltage | | | - | 5 | V |
| $P_{GM}$ | peak gate power | | | - | 20 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | | - | 0.5 | W |
| $T_{stg}$ | storage temperature | | | -40 | 150 | °C |
| $T_j$ | junction temperature | | | - | 125 | °C |

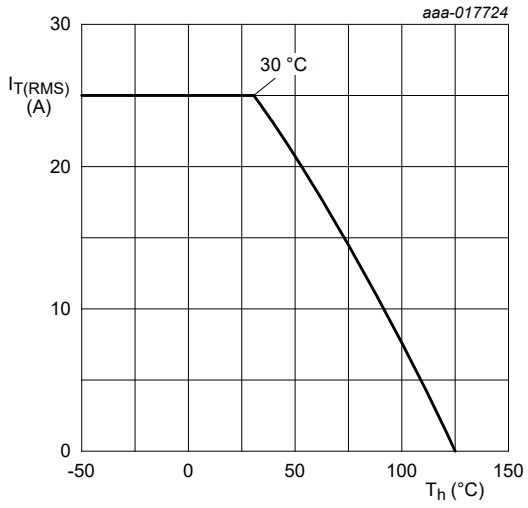
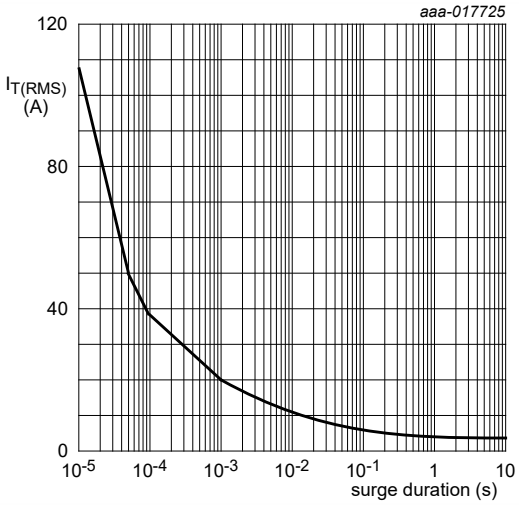
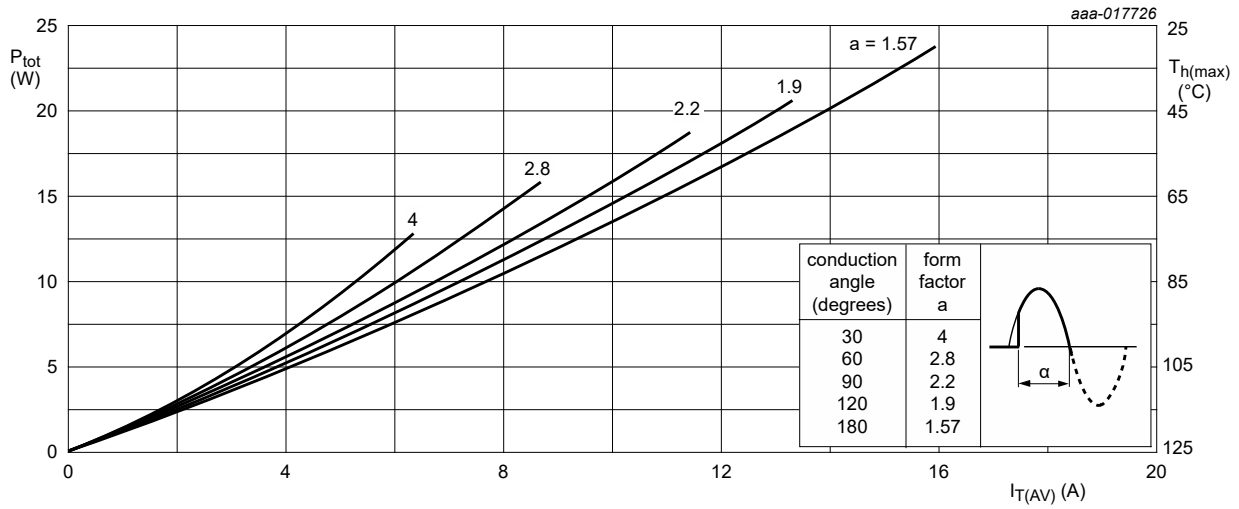



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**




f = 50 Hz; $T_h = 30$ °C

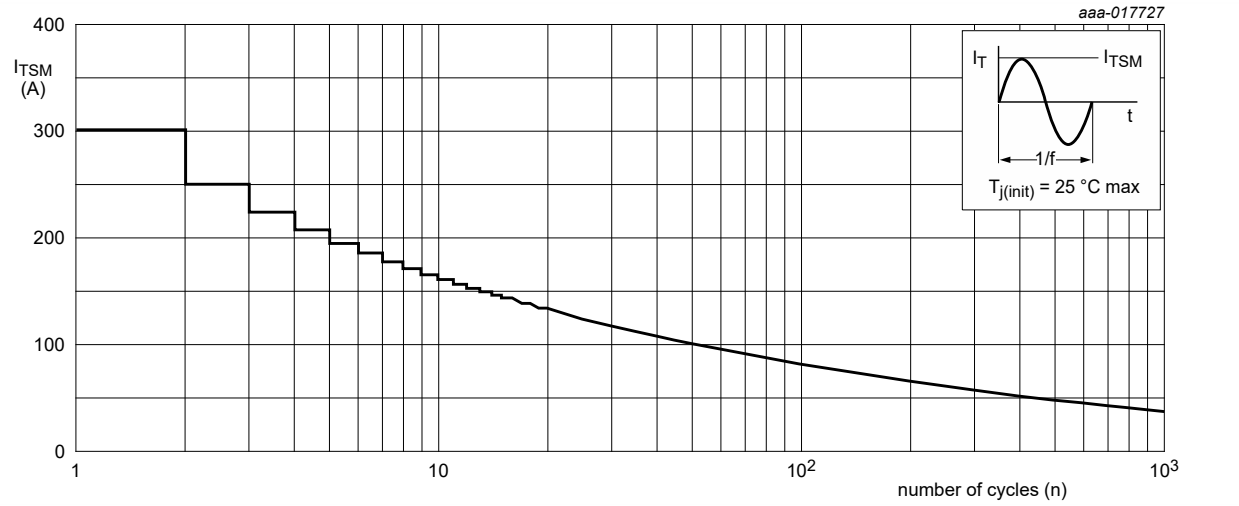
**Fig. 2. RMS on-state current as a function of surge duration; maximum values**




α = conduction angle

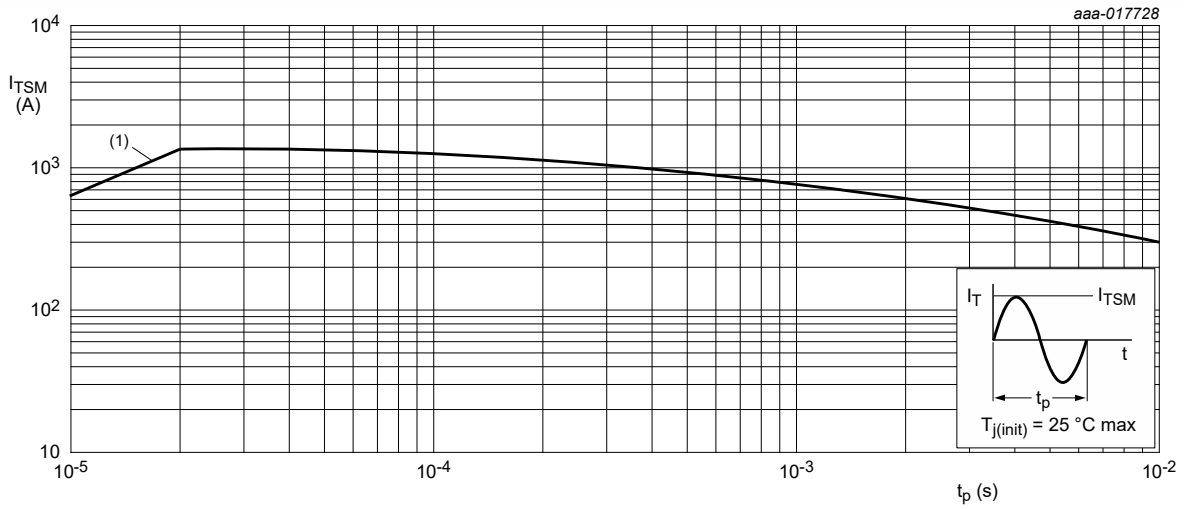
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

**Fig. 3. Total power dissipation as a function of average on-state current; maximum values**




f = 50 Hz

**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**




$t_p \leq 20$ ms

(1) $dI_T/dt$ limit

**Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values**

# 8. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle or half cycle; with heatsink compound; Fig. 6 | | - | - | 4 | K/W |
| | | full cycle or half cycle; without heatsink compound | | - | - | 5.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | | - | 55 | - | K/W |

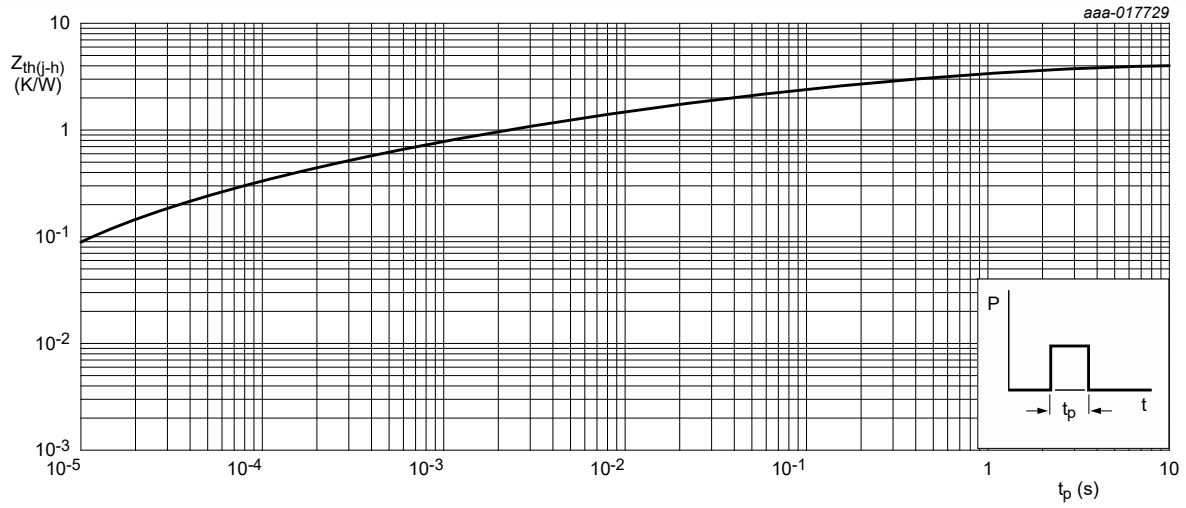



**Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration**

# 9. Characteristics

**Table 6. Characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | | |
| $I_{GT}$ | gate trigger current | $V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C; Fig. 7 | | - | - | 35 | mA |
| $I_L$ | latching current | $V_D$ = 12 V; $I_G$ = 0.1 A; $T_j$ = 25 °C; Fig. 8 | | - | - | 80 | mA |
| $I_H$ | holding current | $V_D$ = 12 V; $T_j$ = 25 °C; Fig. 9 | | - | - | 60 | mA |
| $V_T$ | on-state voltage | $I_T$ = 30 A; $T_j$ = 25 °C; Fig. 10 | | - | 1.1 | 1.5 | V |
| $V_{GT}$ | gate trigger voltage | $V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C; Fig. 11 | | - | 0.6 | 1 | V |
| | | $V_D$ = 800 V; $I_T$ = 0.1 A; $T_j$ = 125 °C; Fig. 11 | | 0.25 | 0.4 | - | V |
| $I_D$ | off-state current | $V_D$ = 800 V; $T_j$ = 125 °C | | - | 0.2 | 1 | mA |
| $I_R$ | reverse current | $V_R$ = 800 V; $T_j$ = 125 °C | | - | 0.2 | 1 | mA |
| **Dynamic characteristics** | | | | | | | |
| $dV_D/dt$ | rate of rise of off-state voltage | $V_{DM}$ = 536 V; $T_j$ = 125 °C; exponential waveform; gate open circuit | | 200 | - | - | V/µs |
| $t_{gt}$ | gate-controlled turn-on time | $I_{TM}$ = 40 A; $V_D$ = 800 V; $I_G$ = 0.1 mA; $dI_G/dt$ = 5 A/µs; $T_j$ = 25 °C | | - | 2 | - | µs |
| $t_q$ | commutated turn-off time | $V_{DM}$ = 536 V; $T_j$ = 125 °C; $I_{TM}$ = 50 A; $V_R$ = 25 V; $(dI_T/dt)_M$ = 30 A/µs; $dV_D/dt$ = 50 V/µs | | - | 70 | - | µs |

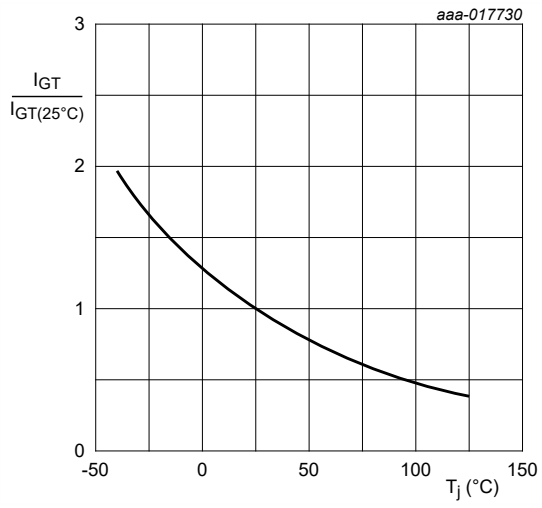



**Fig. 7. Normalized gate trigger current as a function of junction temperature**

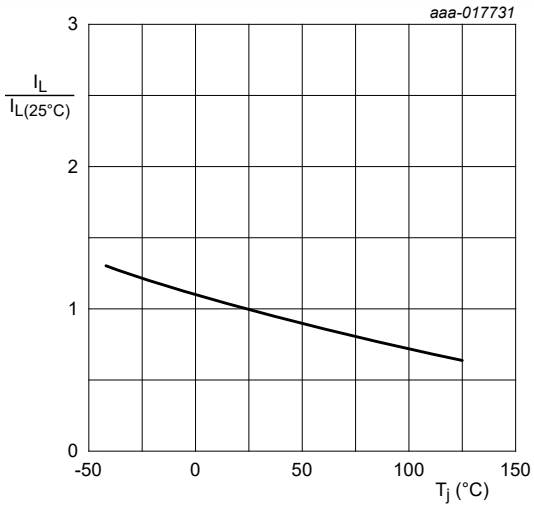



**Fig. 8. Normalized latching current as a function of junction temperature**

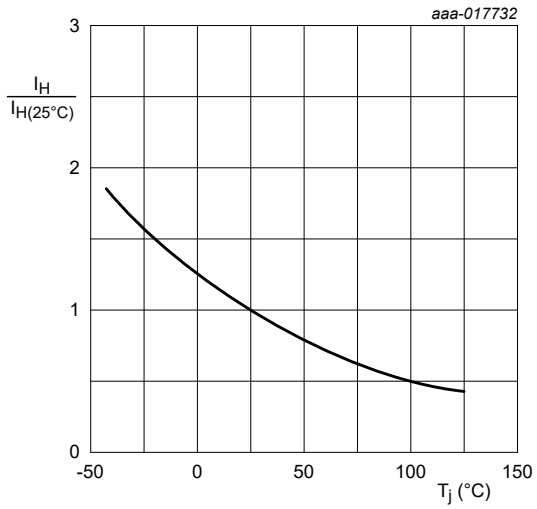
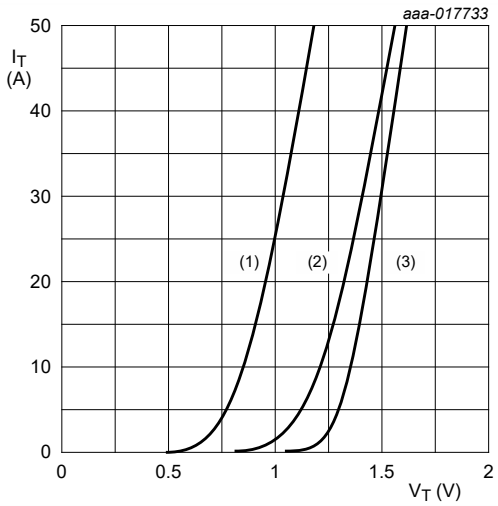



**Fig. 9. Normalized holding current as a function of junction temperature**




$V_o$ = 1.145 V; $R_s$ = 0.009 Ω
(1) $T_j$ = 125 °C; typical values
(2) $T_j$ = 125 °C; maximum values
(3) $T_j$ = 25 °C; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

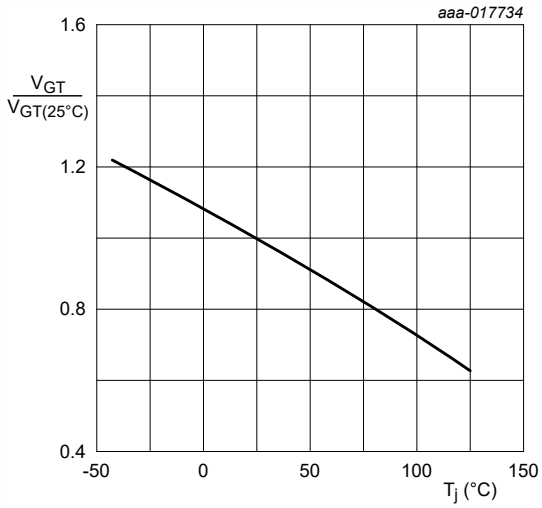
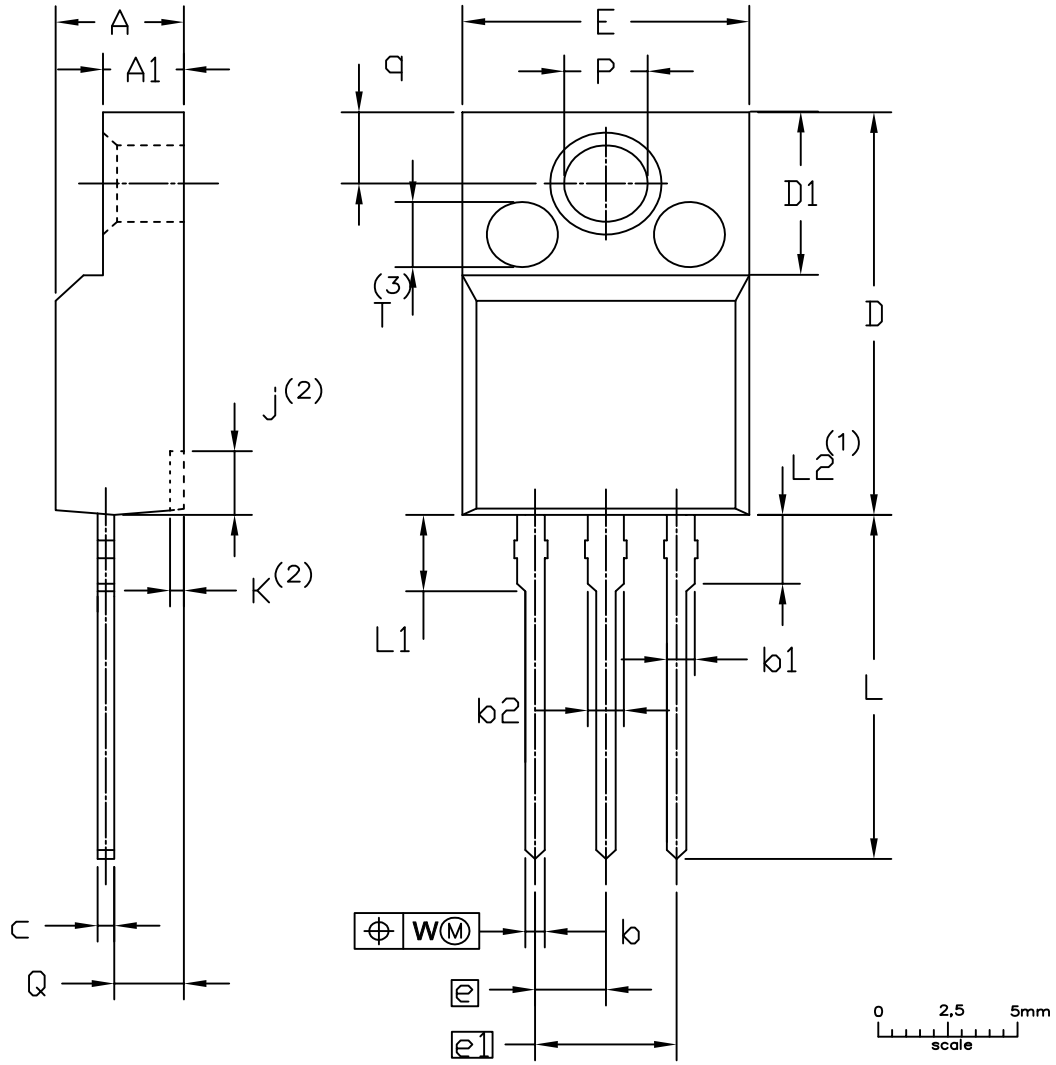



**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

## 10. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" SOT186A




| UNIT | A | $A_1$ | b | $b_1$ | $b_2$ | c | D | $D_1$ | E | e | $e_1$ | j(2) | K(2) | L | $L_1$ | $L_2$(1) max. | P | Q | q | W | T(3) |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 4.6 | 2.9 | 0.9 | 1.1 | 1.4 | 0.7 | 15.8 | 6.5 | 10.3 | 2.54 | 5.08 | 2.7 | 0.6 | 14.4 | 3.30 | 3 | 3.2 | 2.6 | 3.0 | 0.4 | 2.5 |
| | 4.0 | 2.5 | 0.7 | 0.9 | 1.0 | 0.4 | 15.2 | 6.3 | 9.7 | | | 1.7 | 0.4 | 13.5 | 2.79 | | 3.0 | 2.3 | 2.6 | | |

Notes
1. Terminal dimensions within this zone are uncotrolled
2. Dot lines area designs may vary
3. Eject pin mark is for reference only

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT186A | | 3 LEADS TO220F | | | | 2013-11-14 |

Fig. 12. Package outline TO-220F (SOT186A)

# 11. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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[2] The term 'short data sheet' is explained in section "Definitions".
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